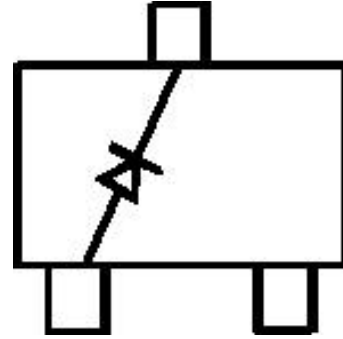


BZX84B2V4-B75



SOT-23封装 内部結構

SOT-23 SURFACE MOUNT ZENER DIODE 表面貼裝穩壓二極管

■ **FEATURES** 特點

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Power dissipation 耗散功率	P_D ($T_a=25^\circ\text{C}$)	350	mW
Forward Current 正向電流	I_F	250	mA
Forward Voltage 正向電壓	V_F (@ $I_F=10\text{mA}$)	0.9	V
Reverse Voltage 反向電壓	V_Z	2.4-75	V
Junctoin and Storage Temperature 結溫和儲藏溫度	T_J, T_{stg}	125°C, -55to+125°C	



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■ ELECTRICAL CHARACTERISTICS 電特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

CHARACTERISTICS	WORK VOLTAGE V_Z (V)		DIFFERENTIAL RESISTANCE r_{dif} (Ω)				TEMP. COEFF. S_Z (mV/K)			Marking
	$I_Z=5\text{mA}$		$I_Z=1\text{mA}$		$I_Z=5\text{mA}$		$I_Z=5\text{mA}$			
TEST CONDITION	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	
BZX84B2V4	2.35	2.45	325	600	80	100	-3.5	-2.1	0	2Z11
BZX84B2V7	2.64	2.76	325	600	80	100	-3.5	-2.1	0	2Z12
BZX84B3V0	2.94	3.06	325	600	80	95	-3.5	-2.1	0	2Z13
BZX84B3V3	3.23	3.37	350	600	85	95	-3.5	-2.4	0	2Z14
BZX84B3V6	3.52	3.68	375	600	85	90	-3.5	-2.4	0	2Z15
BZX84B3V9	3.82	3.98	400	600	85	90	-3.5	-2.5	0	2Z16
BZX84B4V3	4.21	4.39	400	600	85	90	-3.5	-2.5	0	2Z17
BZX84B4V7	4.6	4.8	410	600	80	90	-3.5	-2.5	0	2Z1
BZX84B5V1	4.99	5.2	425	500	50	80	-3.5	-1.4	0.2	2Z2
BZX84B5V6	5.49	5.71	400	480	40	60	-2.7	-0.8	1.2	2Z3
BZX84B6V2	6.07	6.32	80	400	15	40	-2.0	1.2	2.5	2Z4
BZX84B6V8	6.66	6.94	40	150	6	10	0.4	2.3	3.7	2Z5
BZX84B7V5	7.35	7.65	30	80	6	15	1.2	3.0	4.5	2Z6
BZX84B8V2	8.04	8.36	30	80	6	15	2.5	4.0	5.3	2Z7
BZX84B9V1	8.92	9.28	40	80	6	15	3.2	4.6	6.2	2Z8
BZX84B10	9.8	10.2	40	100	6	15	3.8	5.5	7.0	2Z9
BZX84B11	10.8	11.2	50	150	8	20	4.5	6.4	8.0	2Y1
BZX84B12	11.8	12.2	50	150	10	20	5.4	7.4	9.0	2Y2
BZX84B13	12.7	13.3	50	150	10	25	6.0	8.4	10.0	2Y3
BZX84B15	14.7	15.3	50	170	10	30	7.0	9.4	11.0	2Y4
BZX84B16	15.7	16.3	50	200	10	30	9.2	11.4	13.0	2Y5
BZX84B18	17.6	18.4	50	200	10	40	10.4	12.4	14.0	2Y6
BZX84B20	19.6	20.4	50	225	10	45	12.4	14.4	16.0	2Y7
BZX84B22	21.6	22.5	60	225	15	55	14.4	16.4	18.0	2Y8
BZX84B24	23.5	24.5	60	250	20	55	16.4	18.4	20.0	2Y9



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ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD

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CHARACTERISTICS	WORK VOLTAGE V_z (V)		DIFFERENTIAL RESISTANCE r_{dif} (Ω)				TEMP. COEFF. S_z (mV/K)			Marking
	$I_z=2mA$		$I_z=0.5mA$		$I_z=2mA$		$I_z=2mA$			
TEST CONDITION	MIN.	MAX.	TYP.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.	
BZX84B27	26.4	27.6	65	300	25	80	21.4	23.4	25.3	2Y10
BZX84B30	29.4	30.6	70	300	30	80	24.4	26.6	29.4	2Y11
BZX84B33	32.3	33.7	75	325	35	80	27.4	29.7	33.4	2Y12
BZX84B36	35.2	36.8	80	350	35	90	30.4	33.0	37.4	2Y13
BZX84B39	38.2	39.8	80	350	40	130	33.4	36.4	41.2	2Y14
BZX84B43	42.1	43.9	85	375	45	150	37.6	41.2	46.6	2Y15
BZX84B47	44.0	50.0	85	375	50	170	42.0	46.1	51.8	2Y16
BZX84B51	46	48	95	400	60	180	46.6	51.3	57.2	2Y17
BZX84B56	54.8	57.2	110	425	75	200	52.2	58.4	63.8	2Y18
BZX84B62	60.7	63.3	130	450	90	215	58.8	63.9	71.6	2Y19
BZX84B68	66.6	69.4	160	475	110	240	65.6	72.2	79.8	2Y20
BZX84B75	73.5	76.5	200	500	150	255	73.4	81.1	88.6	2Y21



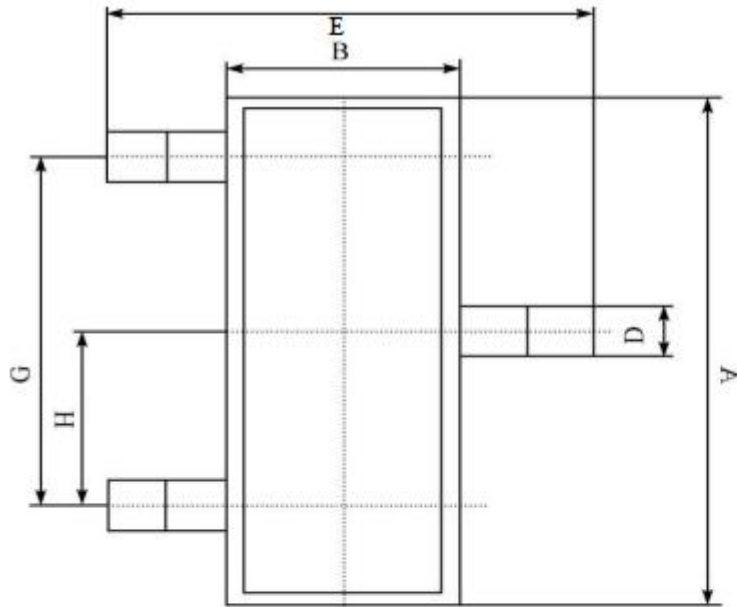
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■ DIMENSION 外形封裝尺寸

單位(UNIT): mm



代碼	範圍(單位:mm)
A	2.80~3.00
B	1.20~1.40
C	0.90~1.10
D	0.30~0.50
E	2.20~2.60
G	1.80~2.00
H	0.90~1.00
J	0.08~0.18
K	0.02~0.12
M	≥0.22
N	0.50~0.70
P	6°~10°

